

BIDIRECTIONAL THYRISTORS

$V_{RM}(V)$ $I_T(A)$	100	200	400	600	I_{GT} (mA)	V_{GT} (V)	Package
0.5	DTA05B	DTA05C	DTA05E		15	2.3	TO92
0.8			DTA08E		10	1.5	TO92
1.0		DTA1C	DTA1E		10	2.0	TO92
2.0	DTA2B	DTA2C	DTA2E		15	2.3	TO202
3.0	DTB3B	DTB3C	DTB3E	DTB3G	30	2.0	TO202
6.0		DTA6C-N	DTA6E-N	DTA6G-N	50	2.0	TO220
		DTM6C-N	DTM6E-N	DTM6G-N	50	2.0	TO220, insulating type
8.0		DTC8C-N	DTC8E-N	DTC8G-N	50	2.0	TO220
		DTM8C-N	DTM8E-N	DTM8G-N	50	2.0	TO220, insulating type
10.0		DTC10C-N	DTC10E-N	DTC10G-N	30	2.0	TO220
		DTM10C-N	DTM10E-N	DTM10G-N	30	2.0	TO220, insulating type
12.0		DTC12C-N	DTC12E-N	DTC12G-N	50	2.0	TO220
		DTM12C-N	DTM12E-N	DTM12G-N	50	2.0	TO220, insulating type

TRIGGER DEVICES

Item	Type Number	Characteristics	Package
Bidirectional Diode	BTD4M	$V_{BO} = 29 \sim 37 V$	DHD
PUT	PTN1	$V_O = 6V, I_P = 5\mu A$	TO92

SENSORS

Type Number	Package	Applications	V_a (V)	V_c (V)	I_c (mA)	P_D (mW)	Remarks
MS-F-06	-	Magnetoresistive Sensor	5.5	-	-	44	$V_{OUT} 0.16 \sim 0.42 mVrms$
MS-G-06	-	Magnetoresistive Sensor	5.5	-	-	44	$V_{OUT} 0.40 \sim 1.1 mVrms$ high output
MS-H-06	-	Magnetoresistive Sensor	5.5	-	-	50	$V_{OUT} 0.30 \sim 1.1 mVrms$ 6mm wide
MS-I-06	-	Magnetoresistive Sensor	5.5	-	-	50	$V_{OUT} 0.46 \sim 1.1 mVrms$ wear-resisting
SHS110	DP4	InSb Hall Element	-	-	12	200	VH 21~55mV(1V, 1kG)
SHS210	CP4	InSb Hall Element	-	-	10	150	VH 21~55mV(1V, 1kG)
SHS211	CP4	InSb Hall Element	-	-	20	150	VH 50~85mV(1V, 1kG)
SHS220	CP4	InSb High Sensitive Hall Element	-	-	20	150	VH 120~200mV(1V, 500G)
SHS260	CP4	GaAs Hall Element	-	7	10	150	VH 60~105mV(5mA, 1kG)
SHS311	SEP4	InSb Hall Element	-	-	20	150	VH 50~90mV(1V, 1kG)
SHS320	SEP4	InSb High Sensitive Hall Element	-	-	20	150	VH 120~275mV(1V, 500G)
SHS361	SEP4	GaAs Hall Element	-	12	-	150	VH 150~200mV(6V, 1kG)